

Substitute for form 1449A/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known				
Application Number	10/731,089			
Filing Date	December 10, 2003			
First Named Inventor	Shinya SASAGAWA et al.			
Art Unit	1765			
Examiner Name	Not Assigned Yet			
Attorney Docket Number	740756-2676			

			U.S. PATENT DOCUME	NTS			
Examiner Initials	Cite No.'	U.S. Patem Document  Number - Kind Code ((f known)	Publication Date MM-DD-YYYY	Name of Patemor or Applicant of Cited Document	Pages, Cohumns, Lines, Who Relevani Passages or Releva Figures Appear	re ni	
MA	1	US-6,596,571 B2	07/22/2003	Arao et al.			
MA	2	US-6,646,287 B1	11/11/2003	Ono et al.			
MA	3	US-6,706,544 B2	03/16/2004	Yamazaki et al.			
M	4 4	US-6,872,604 B2	03/29/2005	Yamazaki et al.			
MA	5	US-6,933,184 B2	08/23/2005	Arao et al.			
MI	6	US-2001/0041392 A1	11/15/2001	Suzawa et al.			
MA	7	US-2001/0048408 A1	12/06/2001	Koyama et al.			
1	A 8	US-2002/0102776 A1	08/01/2002	Yamazaki et al.			
MA	9	US-2002/0163049 A1	11/07/2002	Yamazaki et al.			
M	10	US-2003/0020118 A1	01/30/2003	Kajiwara et al.			
MA	11	US-2003/0062524 A1	04/03/200	Kimura			
M2	12	US-2003/0100151 A1	05/29/2003	Okamoto	,		
MA	13	US-2004/0140472 A1	07/22/2004	Fujimoto et al.			
N	A 14	US-2004/0171242 A1	09/02/2004	Monoe et al.			
MA	15	US-2004/0209409 A1	10/21/2004	Monoe et al.			
		·					
		OTHER PRIOR A	RT – NON PATENT LITEI	EATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>						
MA	16	Y. MISHIMA et al.; "Improved Lifetime of Poly-Si TFTs With a Self-Aligned Gate- Overlapped LDD Structure"; IEEE TRANSACTIONS ON ELECTRON DEVICES; 06/01/2002; Vol. 49; No. 6; PP. 981-985					
MA	17	K. OHGATA et al.; "A New Dopant Activation Technique for Poly-Si TFTs With a Self-Aligned Gate-Overlapped LDD Structure"; IEDM: TECHNICAL DIGEST OF INTERNATIONAL DEVICES MEETING; 12/10/2000; PP. 205-208.					
Examiner Signature		/Maki Angadi/	Da Co	ate 09/	08/2006		

<sup>•</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&</sup>lt;sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at <a href="https://www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

<sup>&</sup>lt;sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.